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28A. Power Devices and Widebandgap Heterostructures (1)

Session Date:	March 9(Thu.), 2023
Session Time:	13:00-14:35
Session Room:	Room A (#301)
Session Chair:	Prof. Jae-Hyun Ryou (University of Houston)
	Prof. Gökhan Atmaca (Hongik University)

[28A-1] [Keynote] **13:00-13:25**

Investigation of β-Ga_2O_3 Material Properties for High Power Applications

Thaddeus J. Asel[1], Adam T. Neal[1], Brenton A. Noesges[1,2], Yunjo Kim[1,3], Kyle J. Liddy[1], Ahmad Islam[1], Kevin Leedy[1], Daniel M. Dryden[1,4], Jeremiah Wiliams[1], Nicholas P. Seplak[1,4], Andrew J. Green[1], John Blevins[1], Kelson D. Chabak[1] and Shin Mou[1]

[1]Air Force Research Laboratory, [2]Azimuth Corporation, [3]ARCTOS, [4]KBR, Inc.

[28A-2] [Invited] **13:25-13:50**

Enhance Gate Reliability and Threshold Voltage Stability of p-GaN Gate High-Electron-Mobility Transistors

Haohao Chen, Junting Chen, Chengcai Wang, Zuoheng Jiang and Mengyuan Hua

Southern University of Science and Technology

[28A-3] **13:50-14:05**

Suppressed Dynamic Avalanche and Enhanced Turn-Off dV/dt Controllability in 3300V Scaled IGBTs

Xiang Zhou, Munetoshi Fukui, Kiyoshi Takeuchi, Takuya Saraya and Toshiro Hiramoto

The University of Tokyo

[28A-4] **14:05-14:20**

High Conduction Band Offset of ALD BeO Film on Wide-Bandgap Semiconductors

Dohwan Jung[1], Yoonseo Jang[1], Prakash R. Sultane[2], Christopher W. Bielawski[2,3] and Jungwoo Oh[1]

[1]Yonsei University, [2]Institute for Basic Science, [3]Ulsan National Institute of Science and Technology

[28A-5] **14:20-14:35**

Effects of Oxide Species on the Reduction of Contact Resistivity of Al/oxide/n-GaN MIS Devices

Jiro Koba[1,2] and Junichi Koike[1]

[1]Tohoku University, [2]JX Nippon Mining & Metals Corporation